

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2214	(257/315).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/29 12:33
L2	1108	memory and peripheral and (trench or opening or hole or groove or via) and liner and isolat\$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 12:31
L3	86	memory and peripheral and (trench or opening or hole or groove or via) and liner and isolat\$5 and (floating adj (gate or electrode))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 12:32
L4	74	memory and peripheral and (trench or opening or hole or groove or via) and liner and isolat\$5 and (floating adj (gate or electrode)) and stack\$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 13:16
L6	434	(257/374).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/29 13:03
L7	2413	(257/774).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/29 13:02
L8	213	(257/397).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/29 13:05
L9	875	(257/510).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/29 13:08

L10	154	(257/523).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/29 13:08
L11	239	(257/524).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/29 13:09
L12	1229	(257/506).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/29 13:09
L13	232	(257/501).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/29 13:10
L14	247	(257/509).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/29 13:10
L15	49391	wu.inv.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 13:13
L16	0	15 and (tin-wei)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 13:14
L19	2093	15 and taiwan	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 13:14

L20	163	19 and wei	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 13:15
L21	47	19 and wei and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 13:15
L22	112010	chen.inv.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 13:13
L23	9	l22 and (po-an)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 13:13
L24	2093	l15 and taiwan	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 13:14
L25	0	l15 and (tin-wei)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 13:14
L26	5823	22 and taiwan	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 13:14
L27	3947	26 and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 13:15

L28	69	27 and po	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 13:15
L29	2	(memory and peripheral and (trench or opening or hole or groove or via) and liner and isolat\$5 and (floating adj (gate or electrode)) and stack\$5).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/29 13:17
L30	1	(memory and peripheral and (trench or opening or hole or groove or via) and liner and isolat\$5 and (floating adj (gate or electrode)) and stack\$5).clm.	US-PGPUB	OR	ON	2005/12/29 13:16